

July 2007

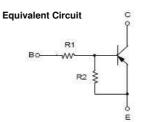
# FJY4005R PNP Epitaxial Silicon Transistor

## **Features**

- · Switching circuit, Inverter, Interface circuit, Driver Circuit
- Built in bias Resistor (R<sub>1</sub>=4.7K $\Omega$ , R<sub>2</sub>=10K $\Omega$ )
- · Complement to FJY3005R







# Absolute Maximum Ratings \* $T_a = 25$ °C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	-50	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-50	V
V <sub>EBO</sub>	Emitter-Base Voltage	-10	V
I <sub>C</sub>	Collector Current	-100	mA
T <sub>STG</sub>	Storage Temperature Range	-55~150	°C
T <sub>J</sub>	Junction Temperature	150	°C
P <sub>C</sub>	Collector Power Dissipation, by R <sub>0JA</sub>	200	mW

С

# Thermal Characteristics\* Ta=25°C unless otherwise noted

R <sub>BJA</sub> Thermal Resistance, Junction to Ambient 600 °C/W	Symbol	Parameter	Max	Units
0071		Thermal Resistance, Junction to Ambient	600	°C/W

# Electrical Characteristics\* T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	MIN	Тур	MAX	Units
V <sub>(BR)CBO</sub>	Collector-Emitter Breakdown Voltage	Ic = -10 uA, IE = 0	-50			V
V <sub>(BR)CEO</sub>	Collector-Base Breakdown Voltage	Ic = -100 uA, I <sub>B</sub> = 0	-50			V
Ісво	Collector-Cutoff Current	Vcb = -40 V, IE = 0			-0.1	uA
hfe	DC Current Gain	Vce = -5 V, Ic = -5mA	30			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	Ic = -10 mA, I <sub>B</sub> = -0.5 mA			-0.3	V
fт	Current Gain - Bandwidth Product	Vce = -10V, Ic = -5 mA		200		MHz
Ccb	Output Capacitance	Vcb = -10 V, IE = 0, f = 1.0 MHz		5.5		pF
V <sub>I(off)</sub>	Input Off Voltage	VcE = -5 V, Ic = -100uA	-0.3			V
V <sub>I(on)</sub>	Input On Voltage	Vce = -0.3V, Ic = -20mA			-2.5	V
R <sub>1</sub>	Input Resistor		3.2	4.7	6.2	ΚΩ
R <sub>1</sub> /R <sub>2</sub>	Resistor Ratio		0.42	0.47	0.52	

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may by impaired.

# **Typical Performance Characteristics**

Figure 1. DC current Gain

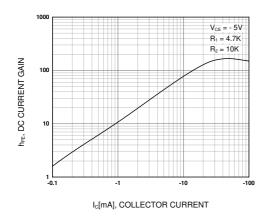


Figure 2. Input On Voltage

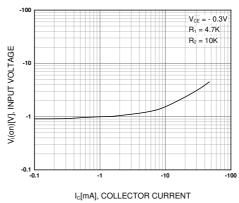


Figure 3. Input off Voltage

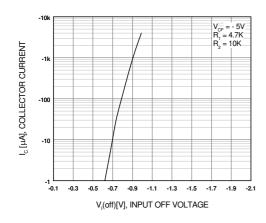
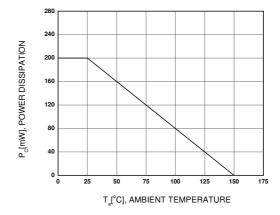
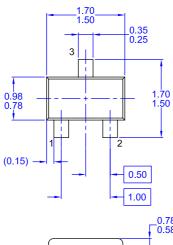


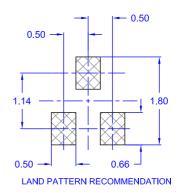
Figure 4. Power Derating

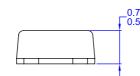


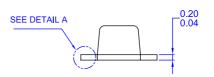
# **Package Dimensions**

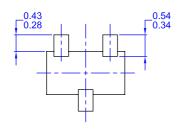
# **SOT-523F**

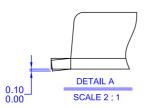












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Dimensions in Millimeters





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Rev. I25